

**LISTING OF THE CLAIMS:**

Claims 1-30 (cancelled).

31. (New) An electronic component operating with acoustic waves, with a multilayer structure, said component comprising:

- 5                   at least one GDE layer;  
                  at least one piezoelectric layer located in close contact with the GDE layer;  
                  a piezoelectric excitation portion having HF electrodes to excite acoustic waves; and  
10                  a piezoelectric tuning portion with control voltage electrodes to change the elasticity modulus of the GDE material directly via a mechanical warping or the combination of the tuning layer and the GDE layer, the excitation portion and tuning portion being realized via the at least one piezoelectric layer.

32. (New) An electronic component according to claim 31, which  
15 has at least one bulk acoustic wave resonator, wherein the piezoelectric excitation layer is a component part of said resonator.

33. (New) An electronic component according to claim 32, which includes an acoustic reflector in which a partial layer of the acoustic reflector is executed as one of an electrode layer and a GDE layer.

- 20                  34. (New) An electronic component according to claim 32, in which electrodes are provided that serve both as HF electrodes to excite bulk acoustic waves and as control voltage electrodes to change the elasticity modulus of the GDE material and for frequency tuning of the bulk acoustic wave resonator.

35. (New) An electronic component according to claim 31, which  
25 includes at least one surface wave component so that the excitation portion forms a piezoelectric substrate of the component.

36. (New) An electronic component according to claim 35, in which one of the control voltage electrodes is arranged on the surface of the piezoelectric layer, which bears interdigital transducers and includes acoustic structures.

37. (New) An electronic component according to claim 31, in which  
5 the GDE layer and at least one piezoelectric layer are separated by an electrode layer.

38. (New) An electronic component according to claim 31, wherein only one piezoelectric layer is provided that serves both as the excitation portion to excite the acoustic wave and as the tuning layer to mechanically warp the GDE  
10 layer.

39. (New) An electronic component according to claim 31, in which the GDE layer is arranged between the excitation layer and the tuning portion.

40. (New) An electronic component according to claim 31, wherein the GDE layer possesses electrically-conductive characteristics and replaces one of  
15 the electrodes.

41. (New) An electronic component according to claim 31, in which the GDE layer and the tuning portion are arranged between two control voltage electrodes.

42. (New) An electronic component according to claim 31, wherein  
20 the excitation portion is comprised of material selected from a group consisting of PZT, ZnO, AlN and GaN.

43. (New) An electronic component according to claim 31, in which the multilayer structure is arranged on a substrate.

44. (New) An electronic component according to claim 43, in which  
25 the carrier substrate comprises a multilayer structure.

45. (New) An electronic component according to claim 43, in which the carrier substrate comprises a multilayer structure with at least one integrated element selected from a group consisting of passive elements, circuit elements and active circuit elements.

5                   46. (New) An electronic component according to claim 43, in which at least one discrete component selected from a group consisting of a passive component and an active component is arranged on the top side of the carrier substrate.

47. (New) An electronic component according to claim 43, in which  
10 at least one chip component is arranged on the top side of the carrier substrate.

48. (New) An electronic component according to claim 47, wherein the chip component is a SAW component.

49. (New) An electronic component according to claim 43, in which at least one circuit element selected from a passive circuit element and an active  
15 circuit element integrated onto the carrier substrate forms at least one part of an adaptation circuit.

50. (New) An electronic component according to claim 43, wherein at least one circuit element integrated onto the carrier substrate forms an element selected from a group consisting of at least one part of an antenna switch, a diode  
20 switch, a high-pass filter, a low-pass filter, a bandpass filter, a band elimination filter, a power amplifier, a diplexer, a duplexer, a coupler, a direction coupler, a balun, a mixer and a storage element.

51. (New) An electronic component according to claim 43, which has at least one discrete circuit element selected from a passive circuit element and  
25 an active circuit element arranged on a top side of the carrier substrate forming a device selected from a group consisting of one part of an antenna switch, a diode switch, a high-pass filter, a low-pass filter, a bandpass filter, a band elimination

filter, a power amplifier, a diplexer, a duplexer, a coupler, a direction coupler, a balun, a mixer and a storage element.

52. (New) An electronic component according to claim 43, which includes at least one part of an adaptation circuit integrated onto the carrier substrate  
5 fashioned as one or more paths for later fine adaptation.

53. (New) An electronic component according to claim 31, which has a carrier substrate that is a multilayer ceramic.

54. (New) An electronic component according to claim 31, which includes a carrier substrate comprised of silicon.

10 55. (New) An electronic component according to claim 31, which includes a carrier substrate comprised of an organic material selected from a plastic and a laminate.

56. (New) An electronic component according to claim 31, which has a substrate and has one or more chip components and one or more discrete,  
15 passive or active circuit elements arranged on the top side of the carrier substrate to represent SMD elements.

57. (New) An electronic component according to claim 31, which has a carrier substrate and at least one chip component and housing being arranged on the top side of the carrier substrate.

20 58. (New) An electronic component according to claim 31, which has a carrier substrate with at least two chip components arranged on the top side of the carrier substrate contained in a common housing.

59. (New) An electronic component according to claim 31, which has a carrier substrate and has at least two separately housed chip components on a  
25 top side of the carrier substrate.

60. (New) An electronic component according to claim 31, wherein at least one of the HF electrodes and the control voltage electrodes comprises a plurality of layers.